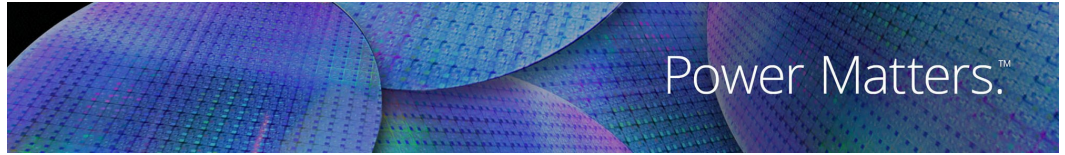


POWER DISCRETES & MODULES

- ▶ Voltage & Current Regulation Diodes
- ▶ Small Signal Diodes and Diode Arrays
- ▶ IGBT
- ▶ Power MOSFET
- ▶ Silicon Carbide (SiC) Semiconductor
- ▶ Power Modules
- ▶ JFET
- ▶ BJT (BiPolar Junction Transistor)
 - BJT Modules (Power Integrated Circuit, PIC)
 - Darlington Transistors
 - Darlington Transistor Array
 - NPN PNP Complimentary Transistor
 - NPN Transistor
 - **PNP Transistor**
- ▶ Legacy Power Discretets & Modules
- ▶ Diode and Rectifier Devices



Home / Power Discretets & Modules / BJT (BiPolar Junction Transistor) / PNP Transistor / 2N5150 (#23287)

2N5150 (#23287)

Product Status
■ In Production

Overview Resources Diagrams Ordering Support

Package ESD Bag
 Carrier:

Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$			0.85	V
DC Current Gain	HFE	70		200	

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Breakdown Voltage, Collector-Base (Emitter O	$V_{BR(CBO)}$			100	V
Collector Current (dc)	I_C			2	A
Collector-Emitter Voltage (Base Open)	V_{CEO}			80	V
Emitter-Base Voltage (Collector Open)	V_{EBO}			6	V
Power Dissipation	P_D			7	W

Alphanumeric Parameter	Value
Quality Level	-

This part can be found in the following product categories:

- Power Discretets & Modules ▶ BJT (BiPolar Junction Transistor)
- Power Discretets & Modules ▶ BJT (BiPolar Junction Transistor) ▶ PNP Transistor